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(54) Title (EN): METHODS FOR FORMING PATTERNED INSULATING LAYERS ON CONDUCTIVE LAYERS AND DEVICES MANUFACTURED USING SUCH METHODS

(54) Title (FR): PROCÉDÉS DE FORMATION DE COUCHES ISOLANTES À MOTIFS SUR DES COUCHES CONDUCTRICES ET DISPOSITIFS FABRIQUÉS À L'AIDE DE TELS PROCÉDÉS

(57) Abstract:

(EN): A method for forming a patterned insulating layer on a conductive layer can include removing an annular region of an insulating layer overlying a perimeter of an opening in a mask by laser ablation. The mask can be removed from the conductive layer to remove an excess portion of the insulating layer disposed on the mask, whereby a remaining portion of the insulating layer defines the patterned insulating layer disposed on the central region of the conductive layer, and a surrounding region of the conductive layer surrounding the central region of the conductive layer is uncovered by the patterned insulating layer.

(FR): Le procédé de formation d'une couche isolante à motifs sur une couche conductrice peut comprendre l'élimination d'une région annulaire d'une couche isolante recouvrant un périmètre d'une ouverture dans un masque par ablation laser. Le masque peut être retiré de la couche conductrice pour retirer une partie excédentaire de la couche isolante disposée sur le masque, une partie restante de la couche isolante délimitant la couche isolante à motifs disposée sur la région centrale de la couche conductrice, et une région environnante de la couche conductrice entourant la région centrale de la couche conductrice n'es pas couverte par la couche isolante à motifs.

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